

Claims 1 to 6 also stand rejected under 35 U.S.C. 102(e), and for 35 U.S.C. 103(a) as being unpatentable over Kang. These rejections are respectfully traversed in light of the amendments to claim 1.

Claim 1 now recites that the active layer and insulating film are formed contiguous the lower portion and sidewall of the stepped substrate in order to distinguish over Kang.

In the present invention, an offset region is formed on the whole lower region of the sidewall and substrate corresponding to the insulating layer as a single region; and on the other hand, in the Kang patent, two offset regions are formed at the both side surfaces centering the insulating film. Relative to that of the Kang patent, the offset structure of the present invention can enhance the flow of the current through the channel.

For the foregoing reasons, reconsideration of the rejections of record is respectfully requested, and an early notice of allowance is earnestly solicited.

Conclusion

The Examiner is respectfully requested to enter this Amendment After Final Rejection in that it raises no new issues. Alternatively, the Examiner is respectfully requested to enter this Amendment After Final Rejection in that it places the application in better form for Appeal.

Should there be any outstanding matters that need to be resolved in the present application, the Examiner is respectfully requested to contact Mr. Joseph A. Kolasch (Reg.

No. 22,463) at the telephone number of the undersigned below, to conduct an interview in an effort to expedite prosecution in connection with the present application.

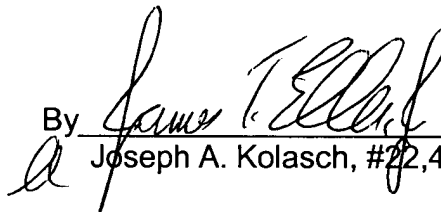
Attached hereto is a marked-up version of the changes made to the application by this Amendment.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

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By

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Attachment: Version with Markings to Show Changes Made

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The claims have been amended as follows:

1. (twice amended) A thin film transistor, comprising:
 - a stepped substrate ~~forming a single Z-shaped cross-section~~ provided with a sidewall between upper and lower ~~portions~~ portion thereof;
 - an active layer formed on the stepped substrate;
 - a gate insulation film formed on a lower portion and a sidewall of the active layer contiguous the lower portion and sidewall of the stepped substrate, respectively;
 - an insulating film formed on a lower portion and a sidewall of the gate insulating film contiguous the lower portion and sidewall of the stepped substrate, respectively;
 - a gate electrode formed on the gate insulation film corresponding to the ~~sidewall~~ sidewalls of the substrate and the insulation film; and
 - ~~an insulation film formed on the gate insulation film between the gate electrode and the lower portion of the substrate; and~~
 - impurity regions in the active layer corresponding to the upper and lower portions of the substrate.

Claim 3 has been deleted.